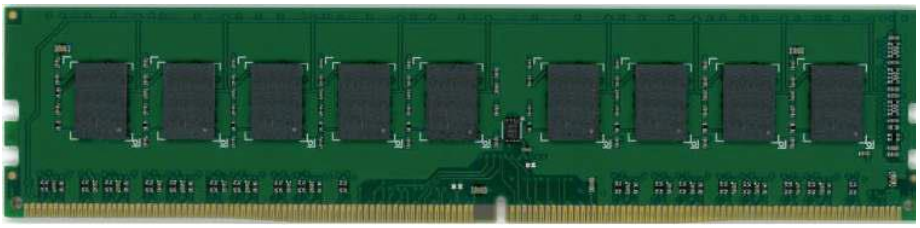
DRF2666E/8GB

8GB - 288-Pin 1Rx8 Unbuffered ECC DDR4 DIMM

Identification
DRF2666E/8GB 1Gx72
8GB 1Rx8 PC4-2666V-E-19



Performance Range
Clock / Module Speed / CL-t_{RCD} –t_{RP}
1333MHz / PC4-2666 / 19-19-19
1200 MHz / PC4-2400 / 17-17-17
1067MHz / PC4-2133 / 15-15-15
933 Hz / PC4-1866 / 13-13-13
800 Hz / PC4-1600 / 11-11-11

Features	Description
288-pin JEDEC-compliant DIMM, 133.35 mm wide by 31.25 mm high Operating Voltage: VDD/VDDQ = 1.2V (1.14V to 1.26V) VPP = 2.5V (2.375V to 2.75V) VDDSPD = 2.25V to 2.75V I/O Type: 1.2 V signaling On-board I^2C temperature sensor with integrated Serial Presence-Detect (SPD) EEPROM Data Transfer Rate: 21.3 Gigabytes/sec Data Bursts: 8 and burst chop 4 mode ZQ Calibration for Output Driver and On-Die Termination (ODT) Programmable ODT / Dynamic ODT during Writes Programmable CAS Latency: 10, 11, 12, 13, 14, 15, 16, 17, 18, and 19 Bi-directional Differential Data Strobe signals Per DRAM Addressability is supported Write CRC is supported at all speed grades DBI (Data Bus Inversion) is supported(x8 only) CA parity (Command/Address Parity) mode is supported Supports ECC error correction and detection 16 internal banks SDRAM Addressing (Row/Col/BG/BA): 16/10/2/2 Fully RoHS Compliant	**DRF2666E/8GB** is an Unbuffered 1Gx72 memory module, which conforms to JEDEC's DDR4-2666, PC4-2666 standard. The assembly is Single-Rank, comprised of nine 512Mbx8 DDR4-2666 SDRAMs. One EEPROM is used for Serial Presence. Both output driver strength and input termination impedance are programmable to maintain signal integrity on the I/O signals in a Fly-by topology.

Notes

Tolerances on all dimensions except where otherwise indicated are ±.13 (.005).

All dimensions are expressed in millimeters [inches]